

International
IR Rectifier

SAFEIR Series
40TPS..

PHASE CONTROL SCR

	$V_T < 1.45V @ 40A$
	$I_{TSM} = 500A$
	$V_{RRM} = 800 - 1200V$

Description/ Features

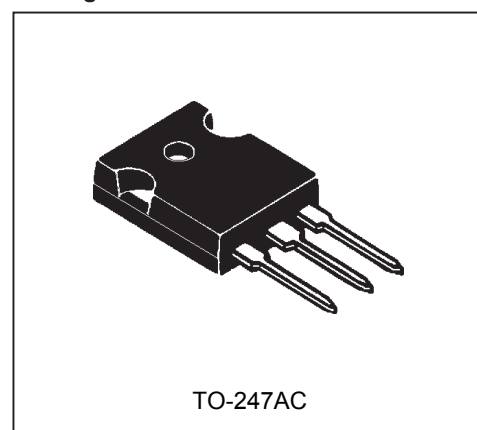
The 40TPS... **SAFEIR** series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125°C junction temperature. Low lgt parts available.

Typical applications are in input rectification (soft start) and these products are designed to be used with International Rectifier input diodes, switches and output rectifiers which are available in identical package outlines.

Major Ratings and Characteristics

Characteristics	40TPS..	Units
$I_{T(AV)}$ Sinusoidal waveform	35	A
I_{RMS}	55	A
V_{RRM}/V_{DRM} Range	800 - 1200	V
I_{TSM}	500	A
$V_T @ 40 A, T_J = 25^\circ C$	1.45	V
dv/dt	1000	V/ μs
di/dt	100	A/ μs
T_J	-40 to 125	°C

Package Outline



Voltage Ratings

Part Number	V_{RRM}/V_{DRM} , max. repetitive peak and off-state voltage V	V_{RSM} , maximum non repetitive peak reverse voltage V	I_{RRM}/I_{DRM} 125°C mA
40TPS08	800	900	10
40TPS12	1200	1300	

Absolute Maximum Ratings

Parameters		40TPS..	Units	Conditions	
I _{T(AV)}	Max. Average On-state Current	35	A	@ T _C = 79° C, 180° conduction half sine wave	
I _{T(RMS)}	Max. Continuous RMS On-state Current As AC switch	55			
I _{TSM}	Max. Peak One Cycle Non-Repetitive Surge Current	500	A	10ms Sine pulse, rated V _{RRM} applied	Initial T _J = T _J max.
		600		10ms Sine pulse, no voltage reapplied	
I ² t	Max. I ² t for Fusing	1250	A ² s	10ms Sine pulse, rated V _{RRM} applied	
		1760		10ms Sine pulse, no voltage reapplied	
I ² √t	Max. I ² √t for Fusing	12500	A ² √s	t = 0.1 to 10ms, no voltage reapplied	
V _{T(TO)1}	Low Level Value of Threshold Voltage	1.02	V	T _J = 125°C	
V _{T(TO)2}	High Level Value of Threshold Voltage	1.23			
r _{t1}	Low Level Value of On-state Slope Resistance	9.74			
r _{t2}	High Level Value of On-state Slope Resistance	7.50	mΩ		
V _{TM}	Max. Peak On-state Voltage	1.85	V	@ 110A, T _J = 25°C	
di/dt	Max. Rate of Rise of Turned-on Current	100	A/μs	T _J = 25°C	
I _H	Max. Holding Current	150	mA		
I _L	Max. Latching Current	300			
I _{RRM} /I _{DRM}	Max. Reverse and Direct Leakage Current	0.5	mA	T _J = 25°C	V _R = rated V _{RRM} /V _{DRM}
		10		T _J = 125°C	
dv/dt	Max. Rate of Rise of Off-state Voltage	40TPS08 40TPS12	500 1000	V/μs	T _J = T _J max., linear to 80% V _{DRM} , R _g -k = open

Triggering

Parameters		40TPS..	Units	Conditions	
P _{GM}	Max. peak Gate Power	10	W		
P _{G(AV)}	Max. average Gate Power	2.5			
I _{GM}	Max. peak Gate Current	2.5	A		
- V _{GM}	Max. peak negative Gate Voltage	10	V		
V _{GT}	Max. required DC Gate Voltage to trigger	4.0		T _J = - 40°C	Anode supply = 6V resistive load
		2.5		T _J = 25°C	
		1.7		T _J = 125°C	
I _{GT}	Max. required DC Gate Current to trigger	270	mA	T _J = - 40°C	
		150		T _J = 25°C	
		80		T _J = 125°C	
		40		T _J = 25°C, for 40TPS08A	
V _{GD}	Max. DC Gate Voltage not to trigger	0.25	V	T _J = 125°C, V _{DRM} = rated value	
I _{GD}	Max. DC Gate Current not to trigger	6	mA		

Thermal-Mechanical Specifications

Parameters			40TPS..	Units	Conditions
T _J	Max. Junction Temperature Range		- 40 to 125	°C	DC operation
T _{stg}	Max. Storage Temperature Range		- 40 to 125		
R _{thJC}	Max. Thermal Resistance Junction to Case		0.6	°C/W	
R _{thJA}	Max. Thermal Resistance Junction to Ambient		40		
R _{thCS}	Max. Thermal Resistance Case to Heatsink		0.2		
			Mounting surface, smooth and greased		
wt	Approximate Weight		6 (0.21)	g (oz.)	
T	Mounting Torque	Min.	6 (5)	Kg-cm (lbf-in)	
		Max.	12 (10)		
Case Style			TO-247AC		

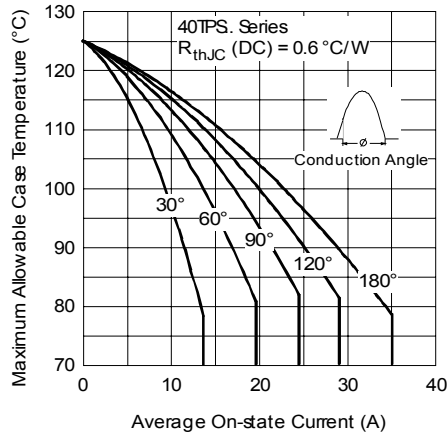


Fig. 1 - Current Rating Characteristics

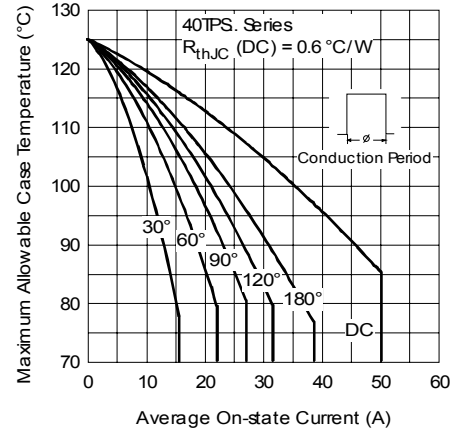


Fig. 2 - Current Rating Characteristics

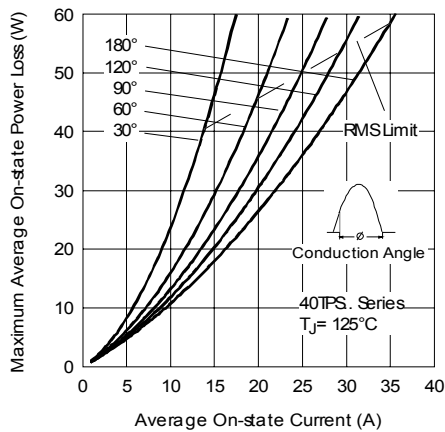


Fig. 3 - On-state Power Loss Characteristics

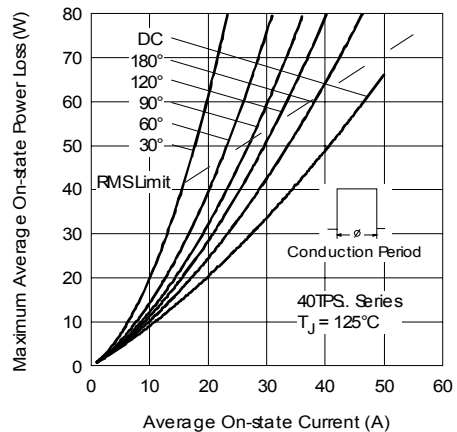


Fig. 4 - On-state Power Loss Characteristics

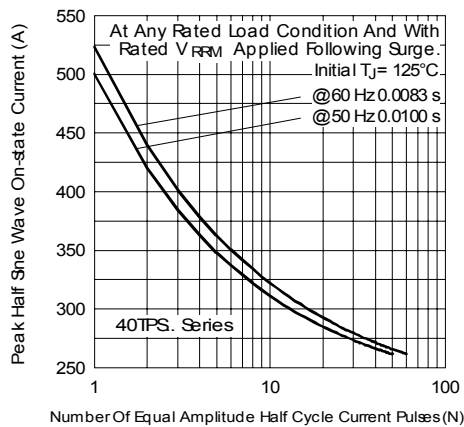


Fig. 5 - Maximum Non-Repetitive Surge Current

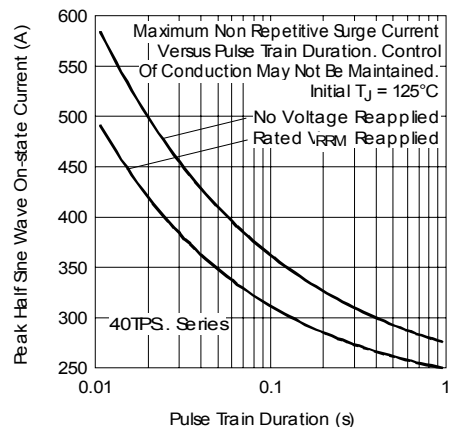


Fig. 6 - Maximum Non-Repetitive Surge Current

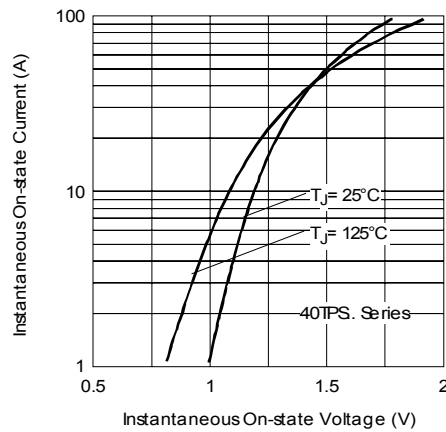


Fig. 7 - On-state Voltage Drop Characteristics

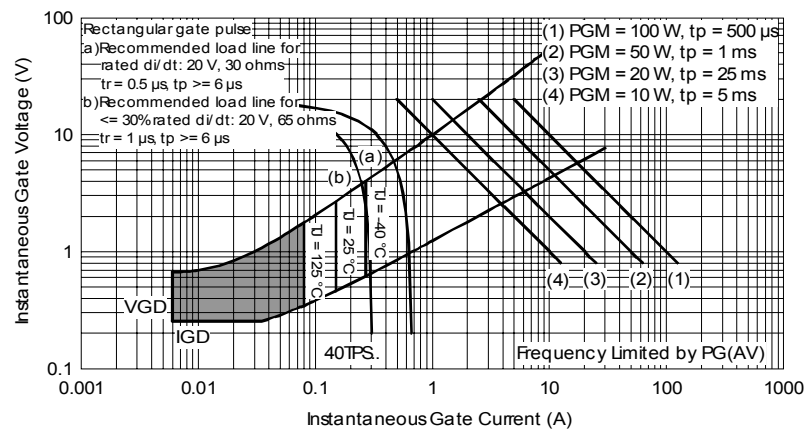


Fig. 8 - Gate Characteristics

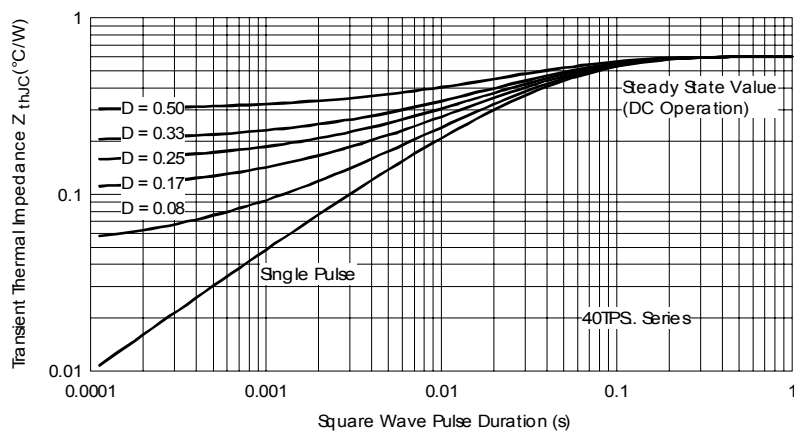
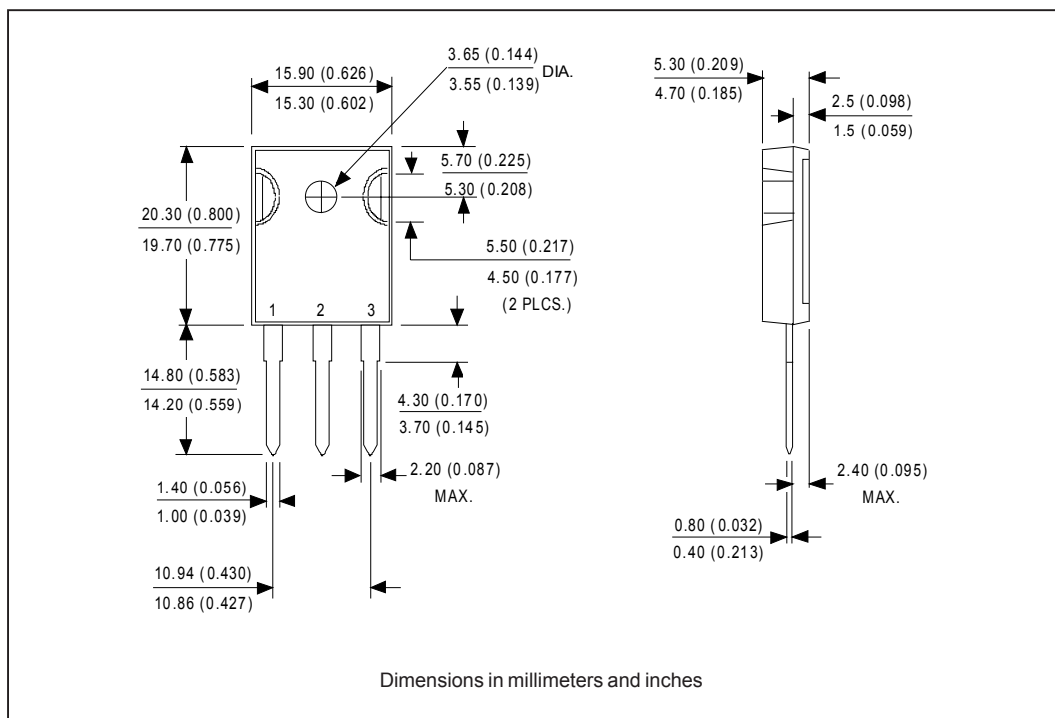


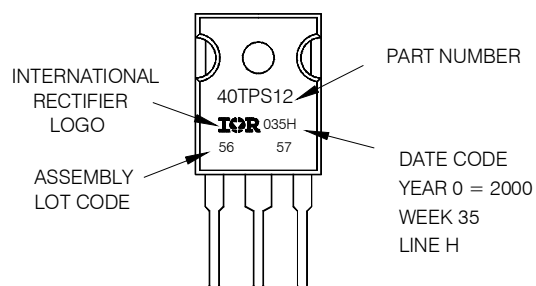
Fig. 9 - Thermal Impedance Z_{thJC} Characteristics

Outline Table



Marking Information

EXAMPLE: THIS IS A 40TPS12
WITH ASSEMBLY
LOT CODE 5657
ASSEMBLED ON WW 35, 2000
IN THE ASSEMBLY LINE "H"



Ordering Information Table

Device Code					
40	T	P	S	12	
1	2	3	4	5	6
1	- Current Rating - Circuit Configuration: T = Thyristor - Package: T = TO-247 - Type of Silicon: S = Standard Recovery Rectifier - Voltage code: Code x 100 = V_{RRM} - None = Standard Igt selection A = Low Igt selection 40mA max. only for 40TPS08A				
					08 = 800V 12 = 1200V

Data and specifications subject to change without notice.
This product has been designed and qualified for Industrial Level.
Qualification Standards can be found on IR's Web site.

International
IR Rectifier

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